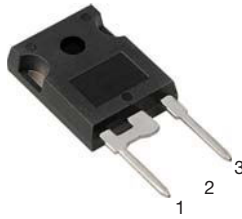
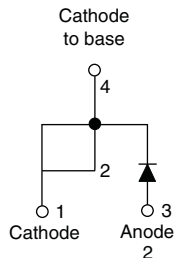


## HEXFRED® Ultrafast Soft Recovery Diode, 25 A


**TO-247AC modified**

**FEATURES**

- Ultrafast and ultrasoft recovery
- Very low  $I_{RRM}$  and  $Q_{rr}$
- Designed and qualified according to JEDEC-JESD47
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

**DESCRIPTION**

VS-HFA25PB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current ( $I_{RRM}$ ) and does not exhibit any tendency to “snap-off” during the  $t_b$  portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25PB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
$I_{F(AV)}$	25 A
$V_R$	600 V
$V_F$ at $I_F$	1.7 V
$t_{rr}$ (yp.	23 ns
$T_J$ max.	150 °C
Diode variation	Single die

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	$V_R$		600	V
Maximum continuous forward current	$I_F$	$T_C = 100\text{ °C}$	25	A
Single pulse forward current	$I_{FSM}$		225	
Maximum repetitive forward current	$I_{FRM}$		100	
Maximum power dissipation	$P_D$	$T_C = 25\text{ °C}$	151	W
		$T_C = 100\text{ °C}$	60	
Operating junction and storage temperature range	$T_J, T_{Stg}$		- 55 to + 150	°C



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	$I_R = 100\text{ }\mu\text{A}$	600	-	-	V
Maximum forward voltage	$V_{FM}$	$I_F = 25\text{ A}$	-	1.3	1.7	
		$I_F = 50\text{ A}$	-	1.5	2.0	
		$I_F = 25\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.3	1.7	
Maximum reverse leakage current	$I_{RM}$	$V_R = V_R$ rated	-	1.5	20	$\mu\text{A}$
		$T_J = 125\text{ }^\circ\text{C}, V_R = 0.8 \times V_R$ rated	-	600	2000	
Junction capacitance	$C_T$	$V_R = 200\text{ V}$	-	55	100	pF
Series inductance	$L_S$	Measured lead to lead 5 mm from package body	-	12	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5, 10	$t_{rr}$	$I_F = 1.0\text{ A}, dl_F/dt = 200\text{ A}/\mu\text{s}, V_R = 30\text{ V}$	-	23	-	ns
	$t_{rr1}$	$T_J = 25\text{ }^\circ\text{C}$	-	50	75	
	$t_{rr2}$	$T_J = 125\text{ }^\circ\text{C}$	-	105	160	
Peak recovery current See fig. 6, 10	$I_{RRM1}$	$T_J = 25\text{ }^\circ\text{C}$	-	4.5	10	A
	$I_{RRM2}$	$T_J = 125\text{ }^\circ\text{C}$	-	8.0	15	
Reverse recovery charge See fig. 7, 10	$Q_{rr1}$	$T_J = 25\text{ }^\circ\text{C}$	-	112	375	nC
	$Q_{rr2}$	$T_J = 125\text{ }^\circ\text{C}$	-	420	1200	
Peak rate of fall of recovery current during $t_b$ See fig. 8, 10	$dl_{(rec)M}/dt1$	$T_J = 25\text{ }^\circ\text{C}$	-	250	-	$\text{A}/\mu\text{s}$
	$dl_{(rec)M}/dt2$	$T_J = 125\text{ }^\circ\text{C}$	-	160	-	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b>						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	$T_{lead}$	0.063" from case (1.6 mm) for 10 s	-	-	300	$^\circ\text{C}$
Thermal resistance, junction to case	$R_{thJC}$		-	-	0.83	K/W
Thermal resistance, junction to ambient	$R_{thJA}$	Typical socket mount	-	-	40	
Thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, flat, smooth and greased	-	0.25	-	
Weight			-	6.0	-	
			-	0.21	-	g
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC modified (JEDEC)	HFA25PB60			

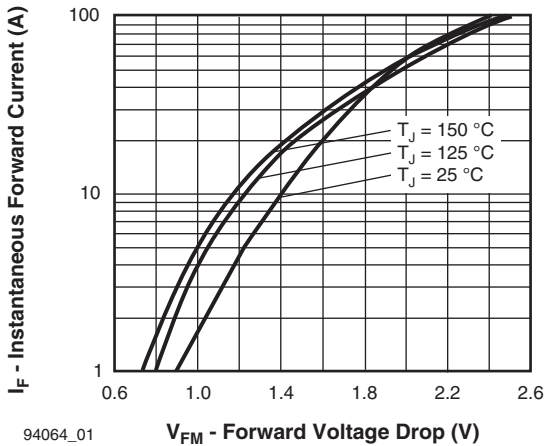


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

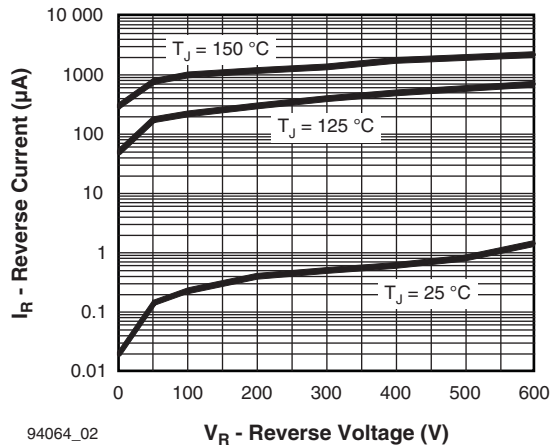


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

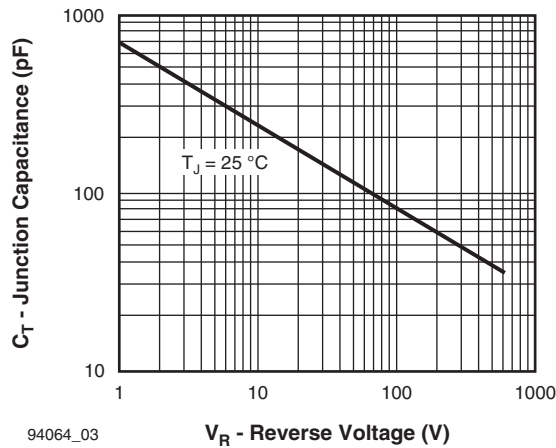


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

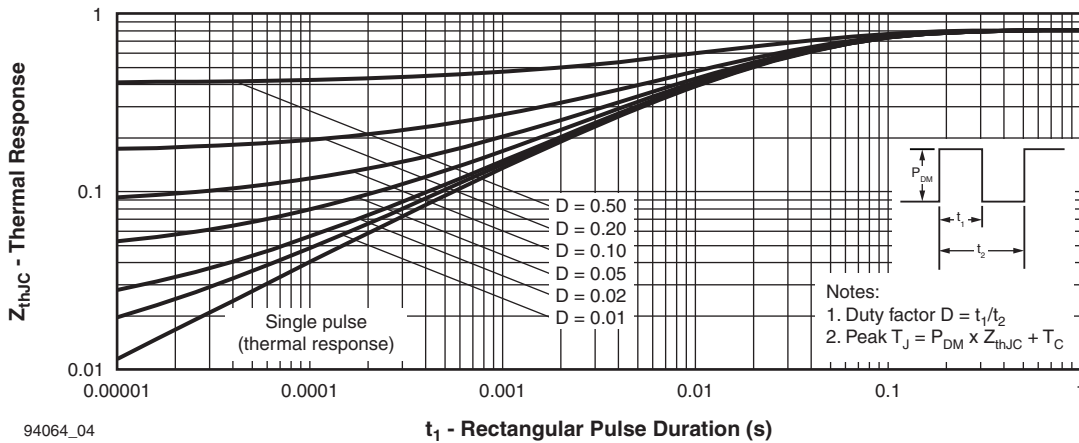


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

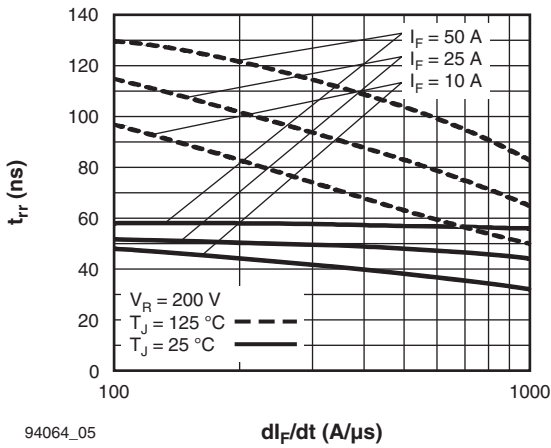


Fig. 5 - Typical Reverse Recovery Time vs.  $di_F/dt$

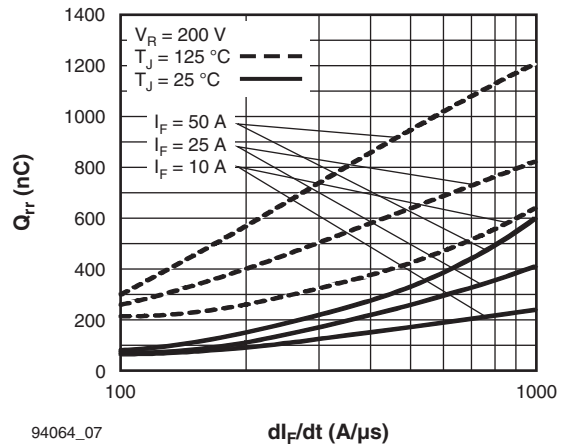


Fig. 7 - Typical Stored Charge vs.  $di_F/dt$

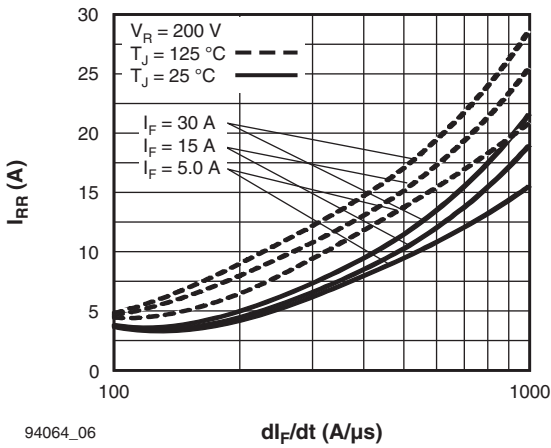


Fig. 6 - Typical Recovery Current vs.  $di_F/dt$

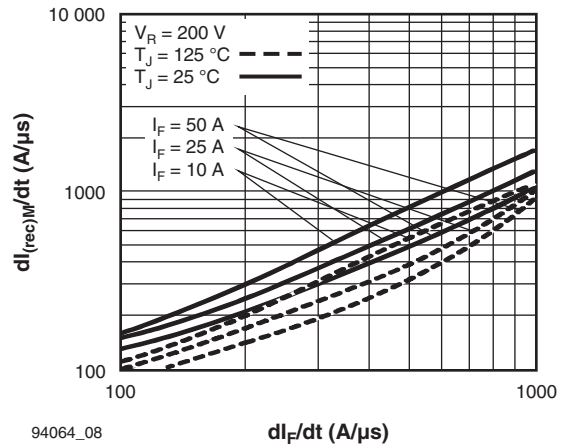


Fig. 8 - Typical  $di_{(rec)M}/dt$  vs.  $di_F/dt$

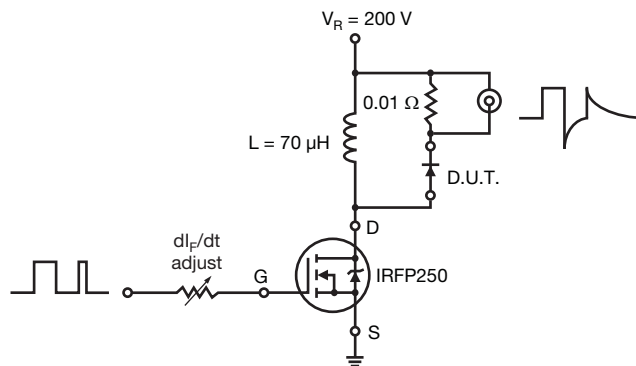
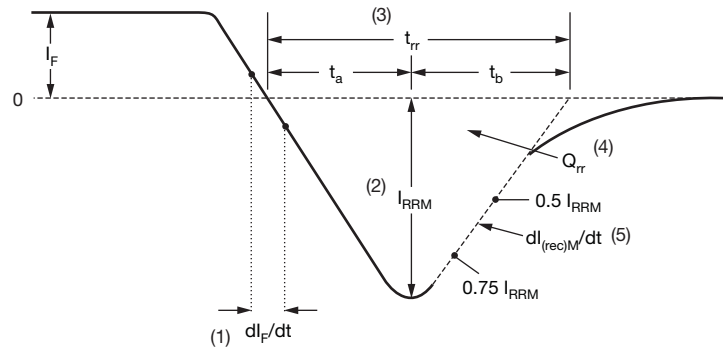


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1)  $di_F/dt$  - rate of change of current through zero crossing

(2)  $I_{RRM}$  - peak reverse recovery current

(3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.

(4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 10 - Reverse Recovery Waveform and Definitions

### ORDERING INFORMATION TABLE

Device code	<b>VS-</b>	<b>HF</b>	<b>A</b>	<b>25</b>	<b>PB</b>	<b>60</b>	<b>PbF</b>
	①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - HEXFRED® family
- 3** - Electron irradiated
- 4** - Current rating (25 = 25 A)
- 5** - PB = TO-247AC modified
- 6** - Voltage rating: (60 = 600 V)
- 7** - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

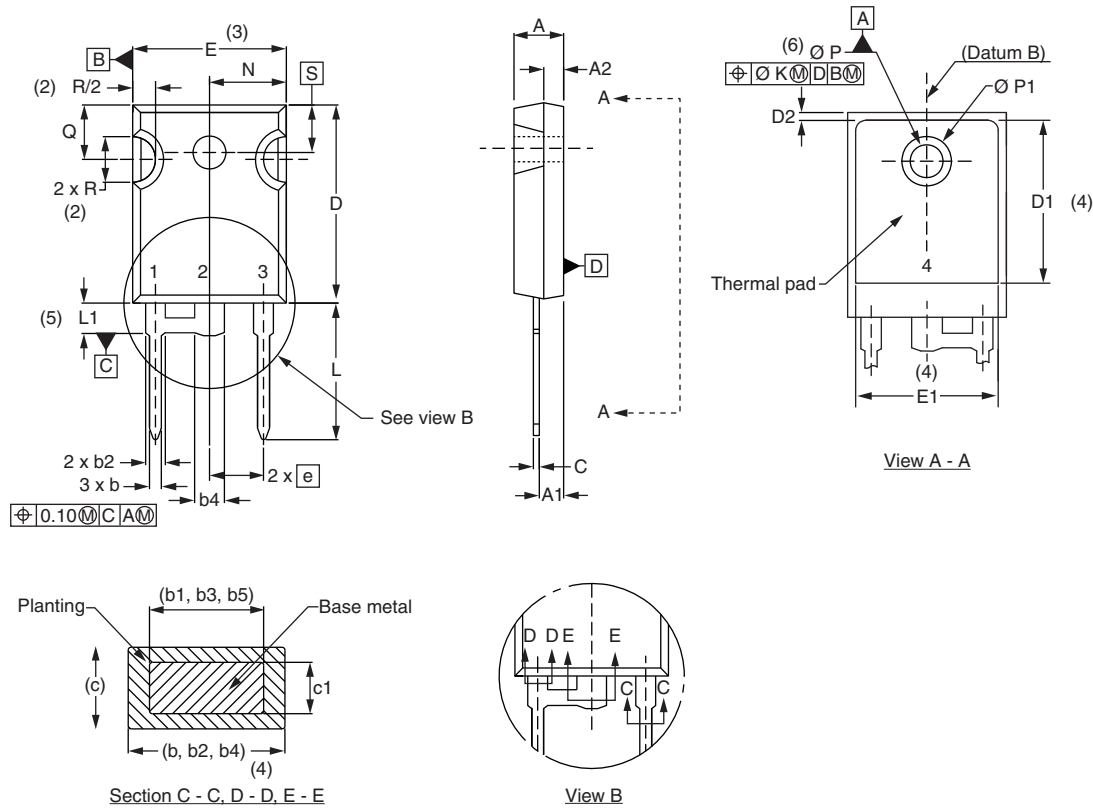
-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-HFA25PB60PbF	25	500	Antistatic plastic tube
VS-HFA25PB60-N3	25	500	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95541">www.vishay.com/doc?95541</a>
Part marking information	TO-247AC modified PbF <a href="http://www.vishay.com/doc?95255">www.vishay.com/doc?95255</a>
	TO-247AC modified -N3 <a href="http://www.vishay.com/doc?95442">www.vishay.com/doc?95442</a>

### TO-247 modified

**DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.17	1.37	0.046	0.054	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.33	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
c	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4
D2	0.51	1.35	0.020	0.053	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
e	5.46 BSC		0.215 BSC		
$\varnothing K$	0.254		0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0.3		
$\varnothing P$	3.56	3.66	0.14	0.144	
$\varnothing P1$	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

**Notes**

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6)  $\varnothing P$  to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

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